

FCHD190N65S3R0

MOSFET – Power, N-Channel, SUPERFET® III, Easy Drive, 650 V, 17 A, 190 mΩ



ON Semiconductor®

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Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

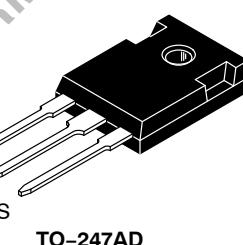
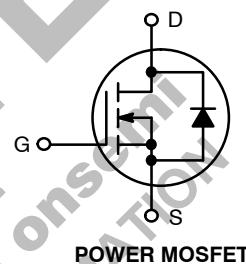
Features

- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 159 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 33 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(\text{eff.})} = 300 \text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter

V_{DSS}	$R_{DS(\text{ON}) \text{ MAX}}$	$I_D \text{ MAX}$
650 V	190 mΩ @ 10 V	17 A



TO-247AD
CASE 340AL

MARKING DIAGRAM



FCHD190N65S3R0 = Specific Device Code

A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCHD190N65S3R0

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain to Source Voltage		650	V
V _{GSS}	Gate to Source Voltage	DC	±30	V
		AC (f > 1 Hz)	±30	V
I _D	Drain Current	Continuous (T _C = 25°C)	17	A
		Continuous (T _C = 100°C)	11	
I _{DM}	Drain Current	Pulsed (Note 1)	42.5	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		76	mJ
I _{AS}	Avalanche Current (Note 1)		2.5	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		1.44	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P _D	Power Dissipation	(T _C = 25°C)	144	W
		Derate Above 25°C	1.15	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 2.5 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 8.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.87	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FCHD190N65S3R0-F155	FCHD190N65S3R0	TO-247AD	Tube	N/A	N/A	30 Units

FCHD190N65S3R0

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	650			V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	700			V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C		0.6		V/°C
		V _{DS} = 650 V, V _{GS} = 0 V		1		μA
I _{DSS}	Zero Gate Voltage Drain Current			0.89		
	V _{DS} = 520 V, T _C = 125°C					
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 0.39 mA	2.5		4.5	V
R _{D(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 8.5 A		159	190	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 8.5 A		10		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz	1350			pF
C _{oss}	Output Capacitance		30			pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	300			pF
C _{oss(er.)}	Energy Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	43			pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 400 V, I _D = 8.5 A, V _{GS} = 10 V (Note 4)	33			nC
Q _{gs}	Gate to Source Gate Charge		7.9			nC
Q _{gd}	Gate to Drain "Miller" Charge		14			nC
ESR	Equivalent Series Resistance		0.5			Ω
SWITCHING CHARACTERISTICS						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 8.5 A, V _{GS} = 10 V, R _g = 4.7 Ω (Note 4)	17			ns
t _r	Turn-On Rise Time		16			ns
t _{d(off)}	Turn-Off Delay Time		42			ns
t _f	Turn-Off Fall Time		6			ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I _S	Maximum Continuous Source to Drain Diode Forward Current			17		A
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current			42.5		A
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 8.5 A		1.2		V
t _{rr}	Reverse Recovery Time	V _{DD} = 400 V, I _{SD} = 8.5 A, dI _F /dt = 100 A/μs	313			ns
Q _{rr}	Reverse Recovery Charge		4.9			μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

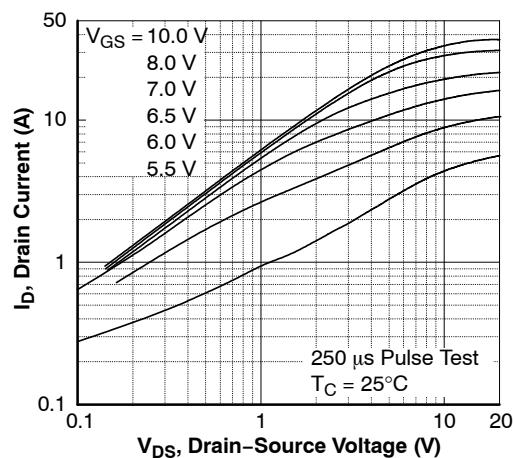


Figure 1. On-Region Characteristics

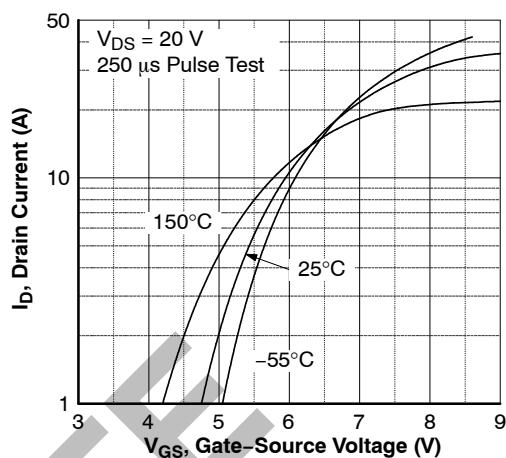


Figure 2. Transfer Characteristics

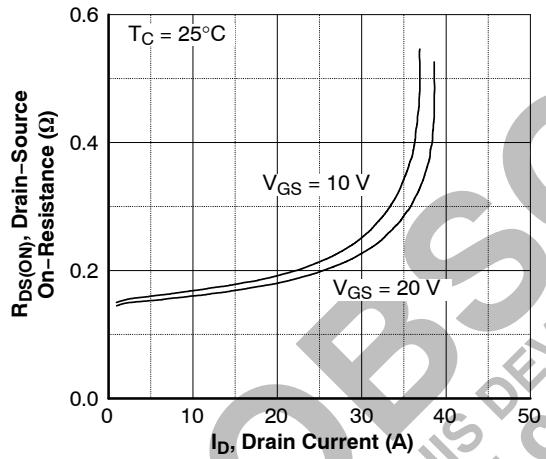


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

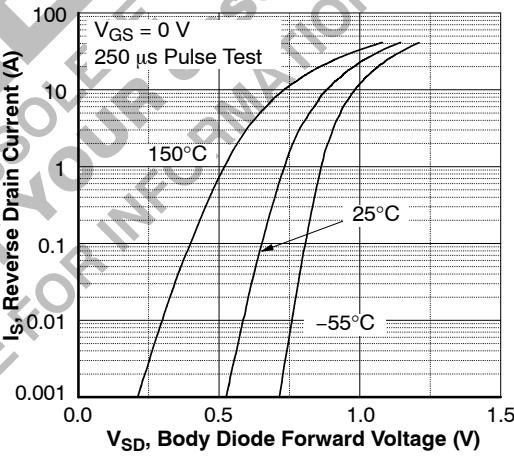


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

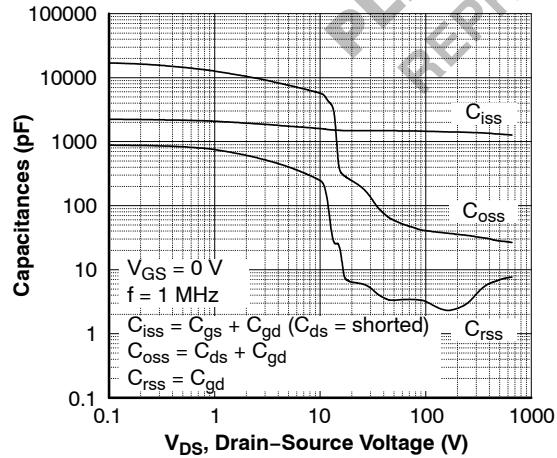


Figure 5. Capacitance Characteristics

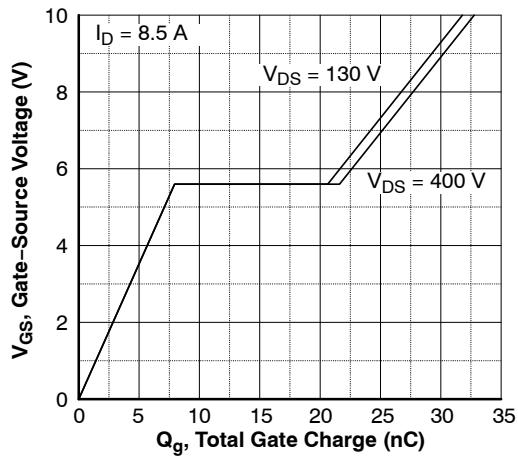


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

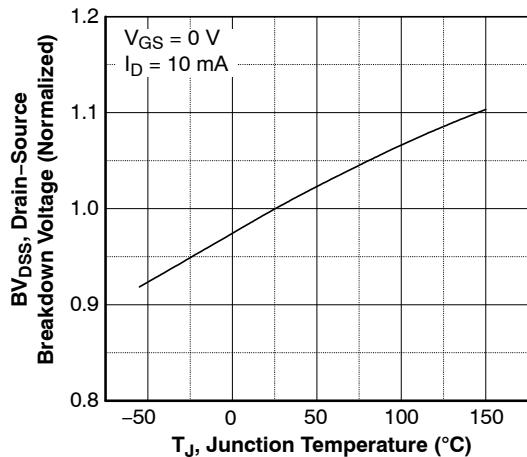


Figure 7. Breakdown Voltage Variation
vs. Temperature

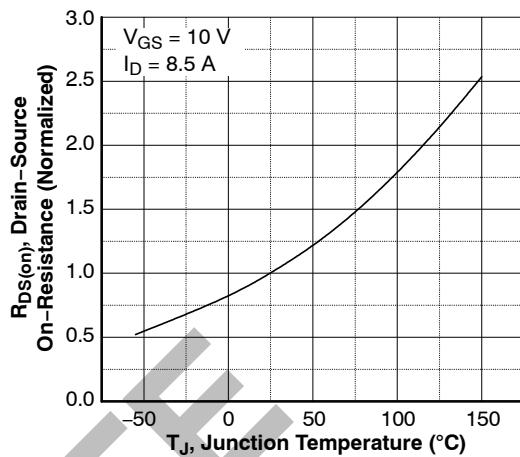


Figure 8. On-Resistance Variation
vs. Temperature

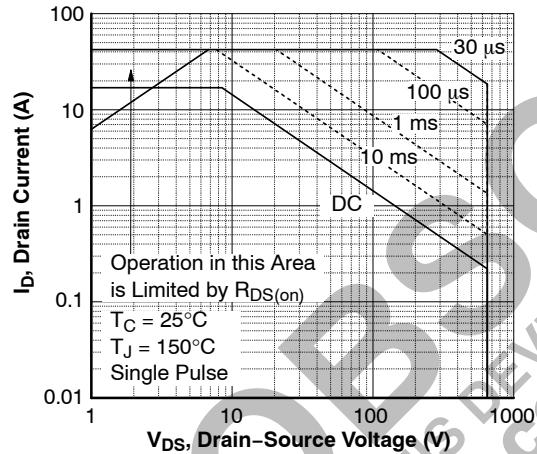


Figure 9. Maximum Safe Operating Area

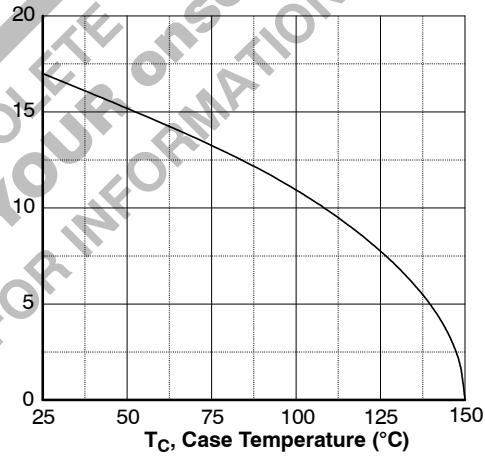


Figure 10. Maximum Drain Current
vs. Case Temperature

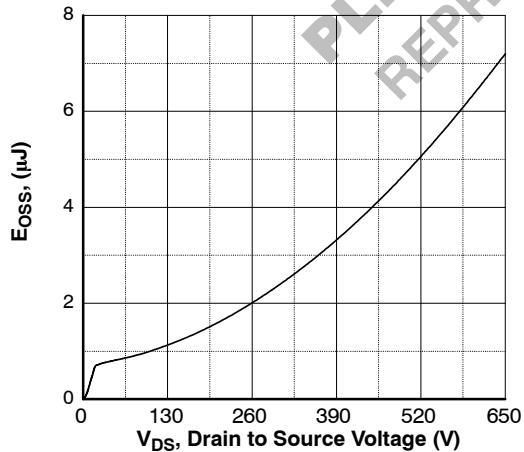


Figure 11. E_OSS vs. Drain to Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

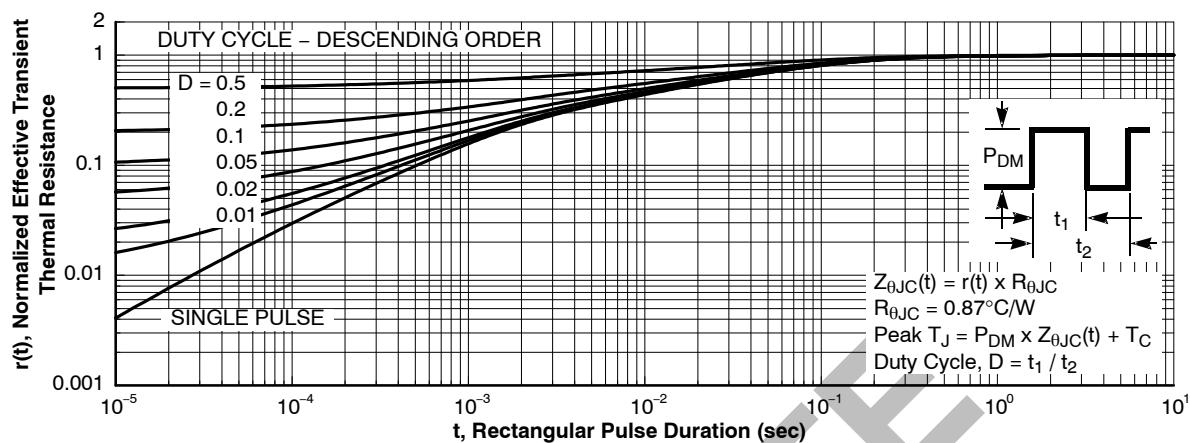


Figure 12. Transient Thermal Response Curve

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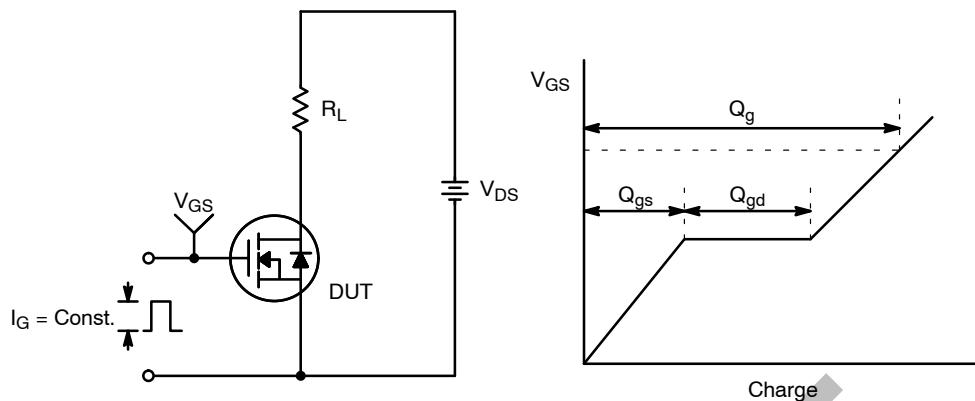


Figure 13. Gate Charge Test Circuit & Waveform

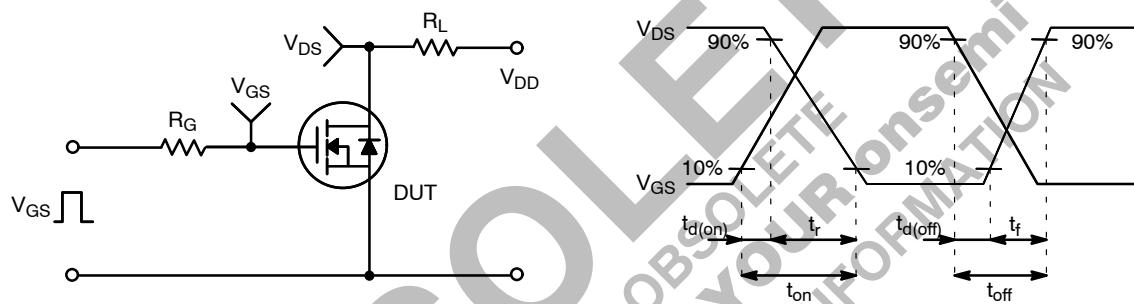


Figure 14. Resistive Switching Test Circuit & Waveforms

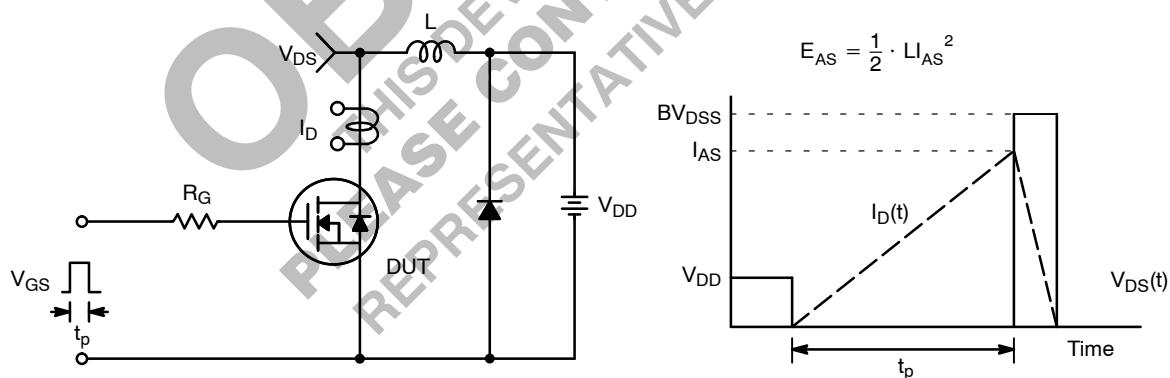


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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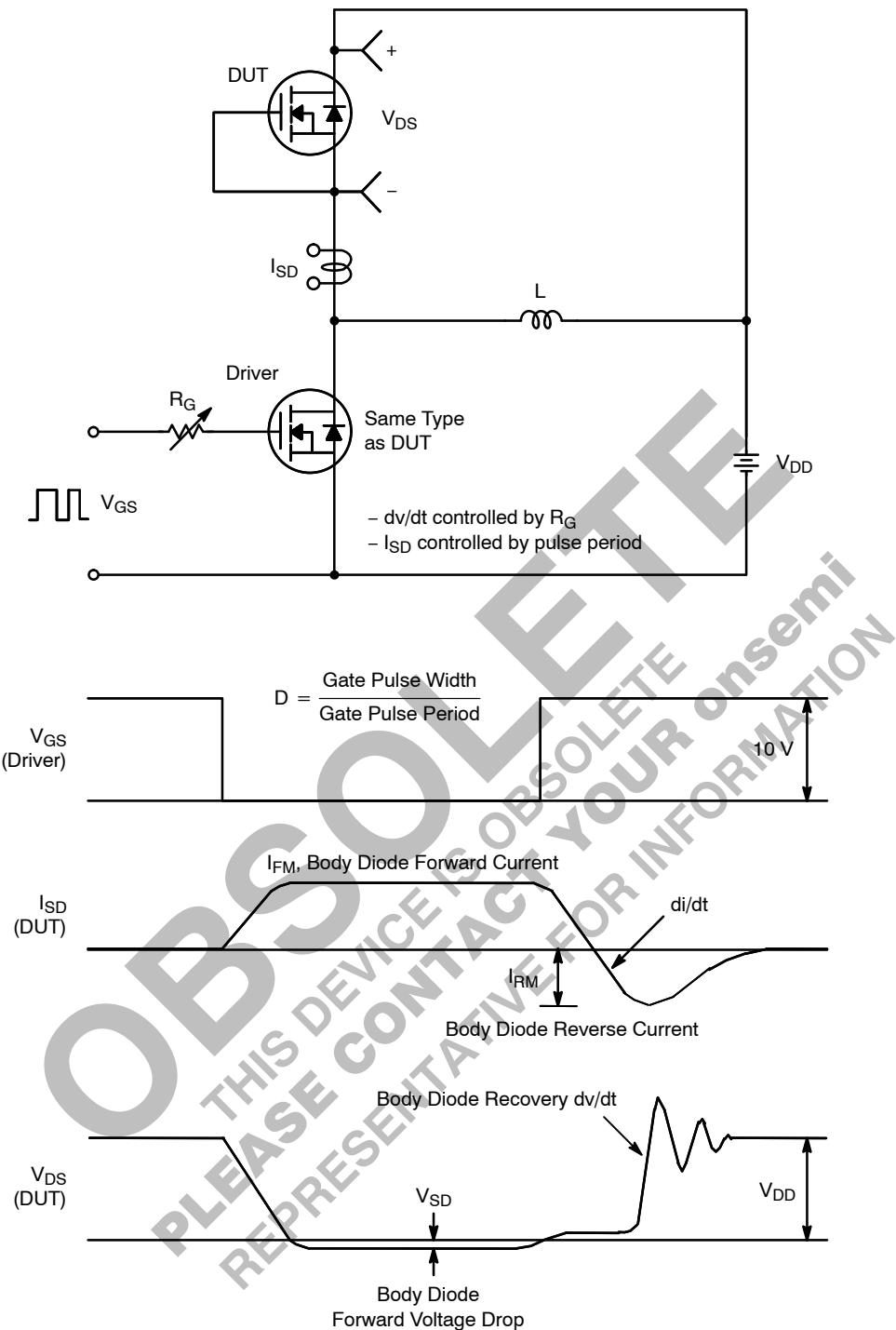
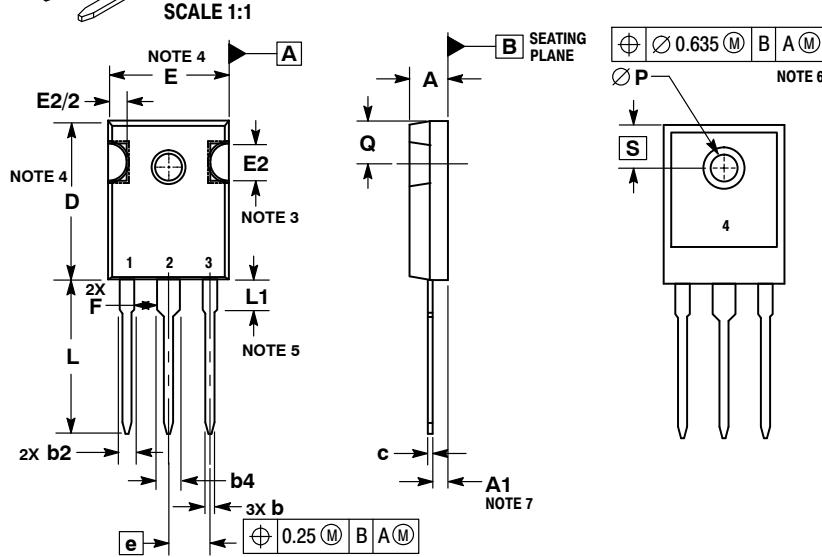
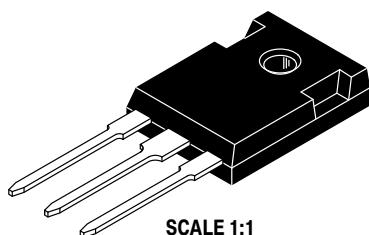


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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CASE 340AL
ISSUE D

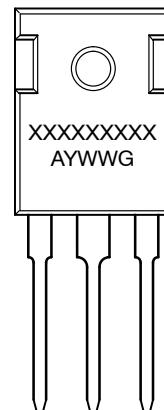
DATE 17 MAR 2017

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ØP SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

MILLIMETERS		
DIM	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

GENERIC
MARKING DIAGRAM*



XXXXXX = Specific Device Code

A = Assembly Location

Y = Year

WW = Work Week

G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot "■", may or may not be present.

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